

TOSHIBA FIELD EFFECT TRANSISTOR SILICON P CHANNEL MOS TYPE

# 2SJ201

HIGH POWER AMPLIFIER APPLICATION

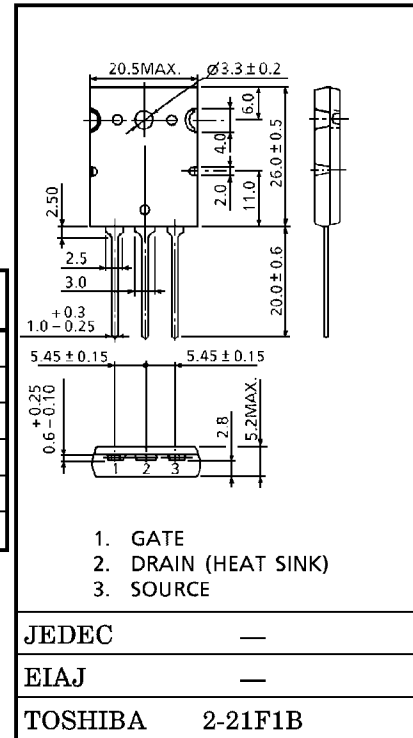
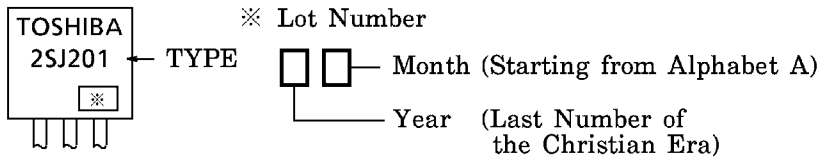
Unit in mm

- High Breakdown Voltage :  $V_{DSS} = -200V$
- High Forward Transfer Admittance :  $|Y_{fs}| = 5.0S$  (Typ.)
- Complementary to 2SK1530

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	$V_{DSS}$	-200	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Drain Current	$I_D$	-12	A
Drain Power Dissipation ( $T_c = 25^\circ C$ )	$P_D$	150	W
Channel Temperature	$T_{ch}$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55~150	$^\circ C$

MARKING



Weight : 9.75g

ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )

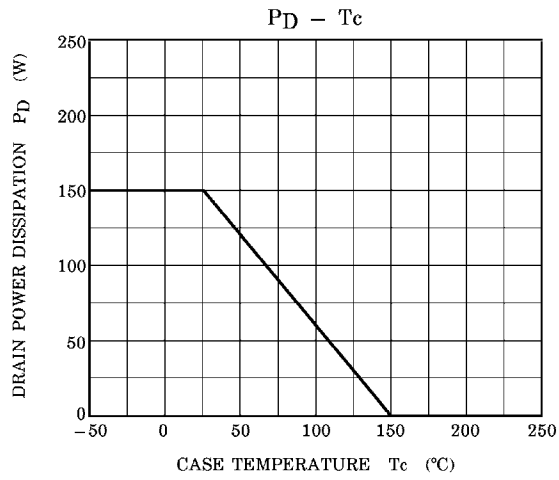
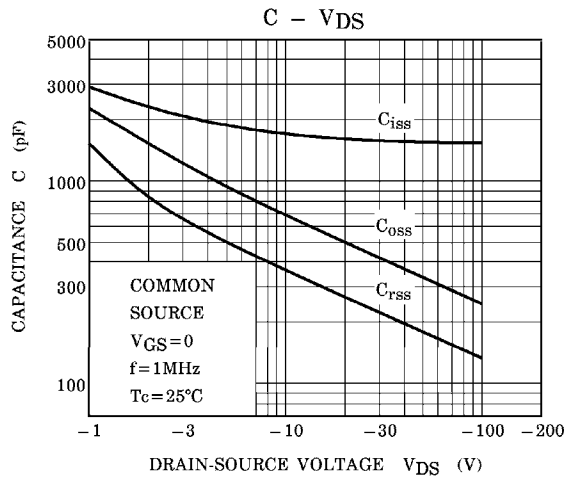
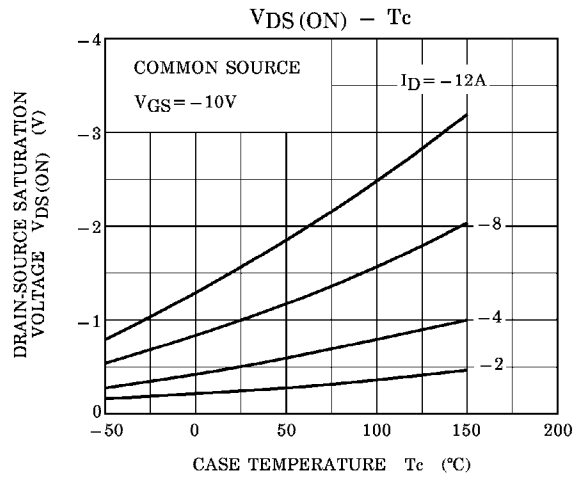
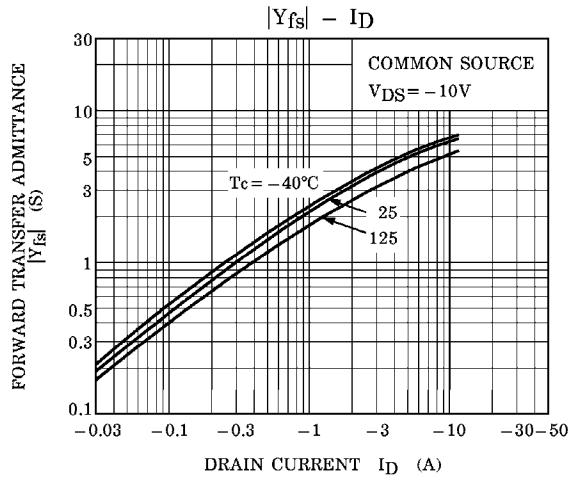
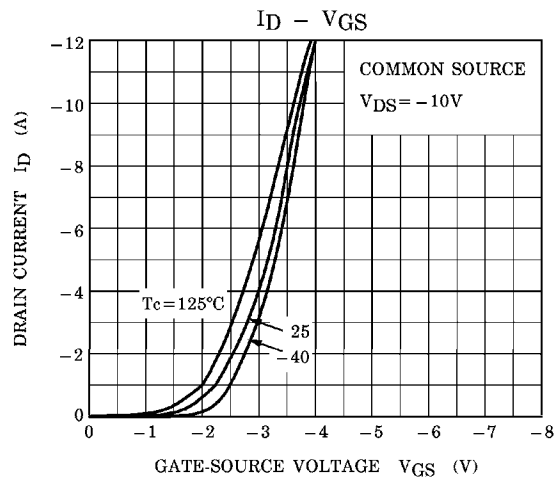
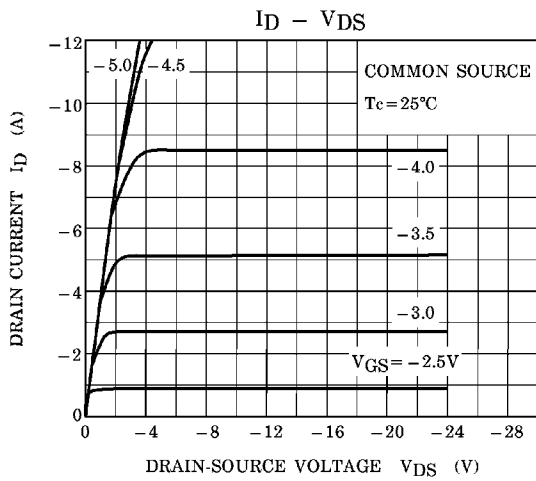
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Drain Cut-Off Current	$I_{DSS}$	$V_{DS} = -200V, V_{GS} = 0$	—	—	-1.0	mA
Gate Leakage Current	$I_{GSS}$	$V_{DS} = 0, V_{GS} = \pm 20V$	—	—	$\pm 0.5$	$\mu A$
Drain-Source Breakdown Voltage	$V(BR)_{DSS}$	$I_D = -10mA, V_{GS} = 0$	-200	—	—	V
Gate-Source Cut-Off Voltage	$V_{GS(OFF)}$ (Note)	$V_{DS} = -10V, I_D = -0.1A$	-0.8	—	-2.8	V
Drain-Source Saturation Voltage	$V_{DS(ON)}$	$I_D = -8A, V_{GS} = -10V$	—	-2.0	-5.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -5A$	—	5.0	—	S
Input Capacitance	$C_{iss}$	$V_{DS} = -30V, V_{GS} = 0, f = 1MHz$	—	1500	—	pF
Output Capacitance	$C_{oss}$	$V_{DS} = -30V, V_{GS} = 0, f = 1MHz$	—	430	—	pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS} = -30V, V_{GS} = 0, f = 1MHz$	—	230	—	pF

(Note)  $V_{GS(OFF)}$  Classification O : -0.8~-1.6, Y : -1.4~-2.8

**This transistor is an electrostatic sensitive device.  
Please handle with caution.**

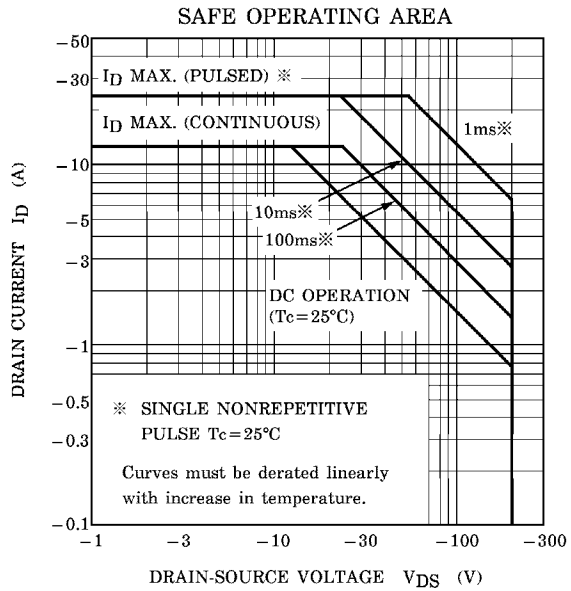
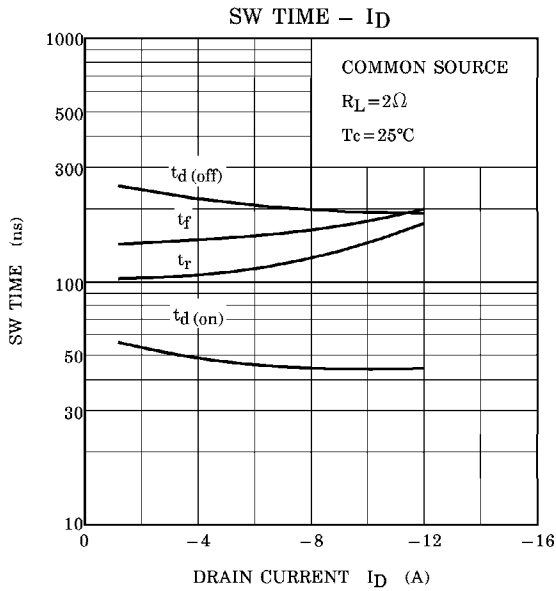
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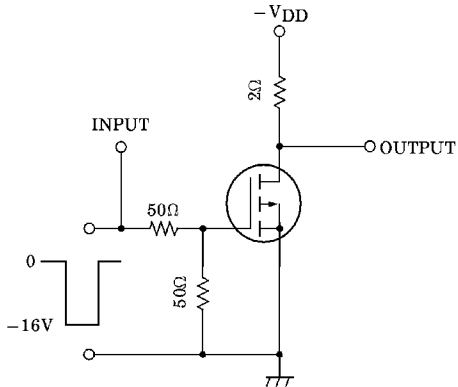


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SWITCHING TIME TEST CIRCUIT



WAVEFORMS

